

# 5V, R/W Preamplifier for 2 Terminal Recording Heads, 2 or 4 Channels

#### GENERAL DESCRIPTION

The XR-4610/4610R are bipolar monolithic integrated circuits commonly used in two terminal thin film recording head applications. The circuitry on the device includes a low noise preamplifier, write current control circuitry and data protection for both two and four channel applications. Power supply fault detection circuitry present on the device disables the write current generator in various power down modes. The read recovery time is improved by control of the read channel common mode output shift when in write mode. The read write device is also available in the XR-4610R option which offers internal 700 Ohm damping resistors.

The XR-4610/4610R operate on a single 5V power supply making them ideal for low power applications. They are available in a variety of low profile packaging options.

#### **FEATURES**

5V Supply Voltage Only Low Power Device (150mW TYP in Read mode) High Performance Circuitry

- -Low Input Noise = 0.70nV/\(\sqrt{Hz}\) max
- -Read Mode Gain = 230V/V
- -Input Capacitance = 48pF max
- -Write Current Range = 10-35mA

Programmable Write Current Source Write Unsafe Detect/Indicator Power Supply Fault Protection Head Short to Ground Protection Enhanced Write to Read Recovery Time Designed for Use With Two Terminal Thin Film Heads

## **APPLICATIONS**

Thin Film Recording Heads in Hard Disk Drives

## **ABSOLUTE MAXIMUM RATINGS**

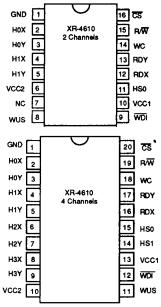
DC Supply Voltage -0.3 to +7 VDC Write Current IW 80mA Digital Input Voltage -0.3 to VCC1 +0.3 VDC Head Port Voltage -0.3 to VCC2 +0.3 VDC Output Current Maximum

> Pins: RDX, RDY

±10mA **WUS** +12mA

Storage Temperature Range -65°C to +150°C

## **PIN ASSIGNMENT**



## ORDERING INFORMATION

Part Number	Package Operating	Temperature
XR-4610/4610R-4CD	20 Pin SOP	0°C to 70°C
XR-4610/4610R-2CD	16 Pin SOP	0°C to 70°C
XR-4610/4610R-4CU	20 Pin SSOP	0°C to 70°C

## SYSTEM DESCRIPTION

The XR-4610/4610R is a low power four channel hard disk drive Read / Write preamplifier for thin film (2 terminal) heads. The XR-4610/4610R provides superior recording performance, and uses only a +5V power supply. Its low power consumption suits it for drives used in battery powered laptop computers.

The read amplifier consists of a 55 MHz bandwidth 0.50 nV/\Hz input noise (both typical) differential amplifier with a fixed gain of 230 V/V. The write driver has a current range of 10 to 35 mA and is disabled automatically when a voltage fault is detected. The write mode also has a write unsafe detection circuit.

## **ELECTRICAL CHARACTERISTICS**

Test Conditions: LH = 1.0 $\mu$ H RH = 30  $\Omega$ ,  $I_W$  = 20mA, f(Data) = 5MHz,  $V_{CC1}$  =  $V_{CC2}$  = 5V  $\pm 5\%$ 

SYMBOL	PARAMETERS	MiN	ТҮР	MAX	UNITS	CONDITIONS
DIGITAL IN	NPUTS					
VIL	Input Low Voltage			8.0	V	
VIH	Input High Voltage	2.0		-	٧.	
liL.	Input Low Current	-400	ľ		μΑ	VIL = 0.8V
lin l	Input High Current		•	100	μА	VIH = 2.0V
WUS VOL	WUS Output Low Voltage		İ	0.5	V	loL = 2mA
VF	VCC1 Fault Voltage			4.2	V	Note 1
	Fault to No Fault				1	
VF	VCC1 Fault Voltage	3.8			٧	İ
	No Fault to Fault					
WRITE CH	IARACTERISTICS					
VWC	Write Current Voltage	1.15		1.35	V	
	Differential Head Voltage Swing	3.4			٧	
ı	-Unselected Head Current			1	mA pk	
	Head Differential Load Capacitance			25	pF	D Onting
	Head Differential Load Resistance	560	700	950		R Option
	Head Differential Load Resistance	4K				
	WDI Transition Frequency	1			MHz	I <sub>W</sub> = 5mA
ıw	Write Current Range	10		35	mA	
- 111.52, 0	(RDX,RDY) < 20 pF, f = 5MHz					
Av BW eni	Differential Voltage Gain Bandwidth -3dB Equivalent Input Noise	180 35	230 55 0.50	260 0.70	V/V MHz nV/√Hz	BW= 15 MHz L <sub>H</sub> = 0,
BW eni	Bandwidth -3dB		55		MHz	BW= 15 MHz L <sub>H</sub> = 0, R <sub>H</sub> = 0
BW eni C <sub>IN</sub>	Bandwidth -3dB Equivalent Input Noise Differential Input Capacitance		55	0.70	MHz nV/√Hz	
BW eni C <sub>IN</sub> R <sub>IN</sub>	Bandwidth -3dB Equivalent Input Noise	35	55 0.50	0.70	MHz nV/√Hz pF	
BW eni C <sub>IN</sub>	Bandwidth -3dB Equivalent Input Noise Differential Input Capacitance Differential Input Resistance Differential Input Resistance	35 835	55 0.50 2K	0.70	MHz nV/√Hz pF Ω	R <sub>H = 0</sub>
BW eni CIN RIN RIN	Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance Differential Input Resistance Differential Input Resistance Dynamic Range to 90% of Gain	35 835 3	55 0.50 2K	0.70	MHz nV/√Hz pF Ω	R <sub>H = 0</sub>
BW eni CIN RIN RIN CMRR	Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance Differential Input Resistance Differential Input Resistance Dynamic Range to 90% of Gain Common Mode Rejection Ratio	35 835 3 45	55 0.50 2K	0.70	MHz nV/√Hz pF Ω Ω mV pp	$R_{H=0}$ R Option  100mV <sub>DD</sub> 5MHz sin
BW eni CIN RIN RIN	Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance Differential Input Resistance Differential Input Resistance Dynamic Range to 90% of Gain	35 835 3	55 0.50 2K	0.70	MHz nV/√Hz pF Ω Ω mV pp dB	R <sub>H = 0</sub> R Option  100mV <sub>pp</sub> 5MHz sin on V <sub>CC</sub>
BW eni CIN RIN RIN CMRR	Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance Differential Input Resistance Differential Input Resistance Dynamic Range to 90% of Gain Common Mode Rejection Ratio	35 835 3 45	55 0.50 2K	0.70	MHz nV/√Hz pF Ω Ω mV pp dB	R <sub>H = 0</sub>
BW eni CIN RIN RIN CMRR	Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance Differential Input Resistance Differential Input Resistance Dynamic Range to 90% of Gain Common Mode Rejection Ratio Power Supply Rejection Ratio Channel Rejection Ratio	35 835 3 45 40	55 0.50 2K	0.70	MHz nV/√Hz pF Ω Ω mV pp dB dB	R <sub>H = 0</sub> R Option  100mV <sub>pp</sub> 5MHz sin on V <sub>CC</sub> Unselected channels driven with100mV <sub>pp</sub>
BW eni CIN RIN RIN CMRR PSRR	Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance Differential Input Resistance Differential Input Resistance Dynamic Range to 90% of Gain Common Mode Rejection Ratio Power Supply Rejection Ratio  Channel Rejection Ratio  Output Offset Voltage	35 835 3 45 40 45	55 0.50 2K	0.70 48	MHz nV/√Hz pF Ω Ω mV pp dB dB dB	R <sub>H = 0</sub> R Option  100mV <sub>pp</sub> 5MHz sin on V <sub>CC</sub> Unselected channels driven with100mV <sub>pp</sub>
BW eni CIN RIN RIN CMRR	Bandwidth -3dB Equivalent Input Noise  Differential Input Capacitance Differential Input Resistance Differential Input Resistance Dynamic Range to 90% of Gain Common Mode Rejection Ratio Power Supply Rejection Ratio Channel Rejection Ratio	35 835 3 45 40 45	55 0.50 2K	0.70 48 300	MHz nV/√Hz pF Ω Ω mV pp dB dB dB	R <sub>H = 0</sub> R Option  100mV <sub>pp</sub> 5MHz sin on V <sub>CC</sub> Unselected channels driven with100mV <sub>pp</sub>

## DC CHARACTERISTICS

SYMBOL	PARAMETERS	MIN	TYP	MAX	UNITS	CONDITIONS
lcc1	VCC1 Supply Current			33	mA	READ Mode
				27	mA	WRITE Mode
I		1		12	mA	IDLE Mode
ICC2	VCC2 Supply Current			11	mA	READ Mode
İ		1		10+ IW	mA	WRITE Mode
ļ			•	400	μА	IDLE Mode
PD	Power Dissipation			230	mW	READ Mode
				190+4IW	mW	WRITE Mode
			35	45	mW	IDLE Mode

Note 1: On the Fault to No Fault transition, all devices will be No Fault at 4.2V.
On the No Fault to Fault transition, all devices will be Fault at 3.8V.

SWITCHING CHARACTERISTICS - Recommended operating conditions apply unless otherwise specified. lw = 20 mA, Lh = 1.0  $\mu$ H, Rh = 30 $\Omega$ , f(Data) = 5 MHz

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	CONDITIONS
	R/W Read to Write		0.1	1.0	μs	R/W to 90% of write current
	Write to Read		0.5	1.0	μs	RW to 90% of 100mV 10 MHz Read signal envelope
	CS Unselect to Select		0.4	1.0	μs	CS to 90% of write current or to 90% of 100mV 10MHz Read signal envelope
	Select to Unselect		0.4	1.0	μs	CS to 10% of write current
	HS0,1 to any Head		0.2	1.0	μs	To 90% of 100mV 10MHz Read signal envelope
TD1 TD2	WUS: Safe to Unsafe Unsafe to Safe	0.6	2.0 0.2	3.6 1.0	μs μs	
TD3	Head Current:  WDI to Ix - Iy  Asymmetry			32 1.0	ns ns	Lh = 0, Rh = 0 from 50% level WDI has 1 ns rise/fall time

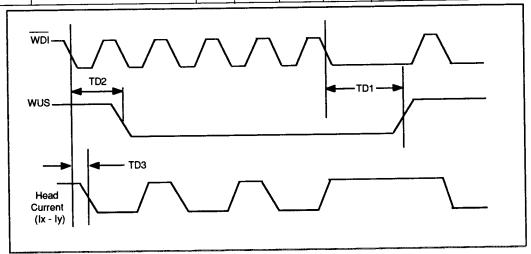


Figure 1. Write Mode Timing Diagram

## PIN DESCRIPTION

Name	1/0	Description	Name	I/O	Description
HS0,HS1	i	Head Select. Select one of four heads.	H0X-H3X; H0Y-H3Y	I/O	X,Y Head Connections
cs	1	Chip Select. High inhibits the chip.	RDX, RDY	0	X,Y Read Data. Differential read data output.
R/W	1	Read/Write. High selects Read mode.	wc		Write Current. Used to set the magnitude of the write current.
WUS *	0	Write Unsafe. High indicates an unsafe writing condition.	VCC1	1	+5V Supply
WDI	I	Write Data In. Changes the direction of the current in the recording head.	VCC2	I	+5V Supply for Write current drivers.
	•	rootioning floud.	GND	1	Ground

<sup>\*</sup> These signals can be wire OR'ed.

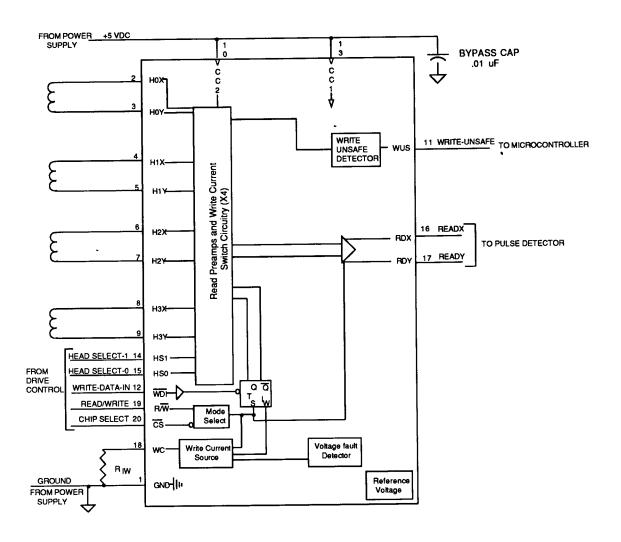


Figure 2. IC Interconnection and Block Diagram

## CIRCUIT OPERATION

The XR-4610 read/write device is intended for use in thin film head hard disk drives with up to four heads. Head selection and mode selection instructions are shown in Tables 1 and 2 respectively. The TTL inputs R/W and CS protect from accidental write current by internal pull up resistors. HSO and HS1 have internal pull down resistors. The pin descriptions are shown on page 4.

#### Read Mode

In read mode operation, the low noise preamplifier circuit reads and amplifies pulses detected on the disk surface caused by magnetic transitions in the media. In this mode write current operations are disabled. RDX and RDY are emitter follower outputs which provide differential read data output pulses. These should be AC coupled to the load. In Write mode and in Idle mode these outputs go into a high impedance state. This allows wire-oring of these outputs in multi-chip applications where more than four head capability is required.

## Write Mode

Write mode is selected when both R/W and  $\overline{CS}$  are taken low. The head current direction of the selected head is toggled by each negative going transition on the write data input pin,  $\overline{WDI}$ . A preceding read or idle mode select initializes the write data flip-flop to pass current through the X side of the head. This current is set by and external resistor, Rw, where:

## MODE DESCRIPTION

HS1	HS0	Head
0	0	0
0	1	1
1	0	2
1	1	3

Table 1. Head Select

Rw is connected between the pins WC and GND. The actual head current is also a function of the head resistance and external wire resistance (Rh) and the damping resistance (Rd), so that:

$$Ix,y = \frac{Iw}{1 + Rh/Rc}$$

The write unsafe detector is also activated in this state.

The pin WUS is an open collector output which should be tied to VCC by a  $2K\Omega$  to  $10K\Omega$  resistor.

## Idle Mode

This mode is selected by taking the pin CS high. The pins RDX and RDY are placed in a high impedance mode to minimize device power consumption and allow another chip to drive these common lines.

## **Voltage Fault**

The write current function is disabled when either a voltage fault or power startup mode is detected, to avoid going into Write mode and contaminating the disks.

The following conditions will indicate a Write Unsafe, but will not stop the Write operation:

- -Device in Read Mode
- -Chip Disabled
- -WDI Frequency too Low
- -No Write Current
- -Head Opened

<u>cs</u>	R/W	Mode
Q	0	Write
0	1	Read
1	0	ldle
1	1	ldle

Table 2. Mode Select